UE4010 Autumn 2006 Part A

Each part of each question carries equal marks.
The body effect may be ignored in each question.
The following equation is given for the drain current of an NMOS in saturation:

$$I_D = \frac{K_n^{'}}{2}\frac{W}{L}(V_{GS}-V_{tn})^2(1+\lambda_n V_{DS})$$

For dc biasing calculations take $\lambda_n=\lambda_p=0$.
In each question, capacitances other than those mentioned may be ignored.

Question 1

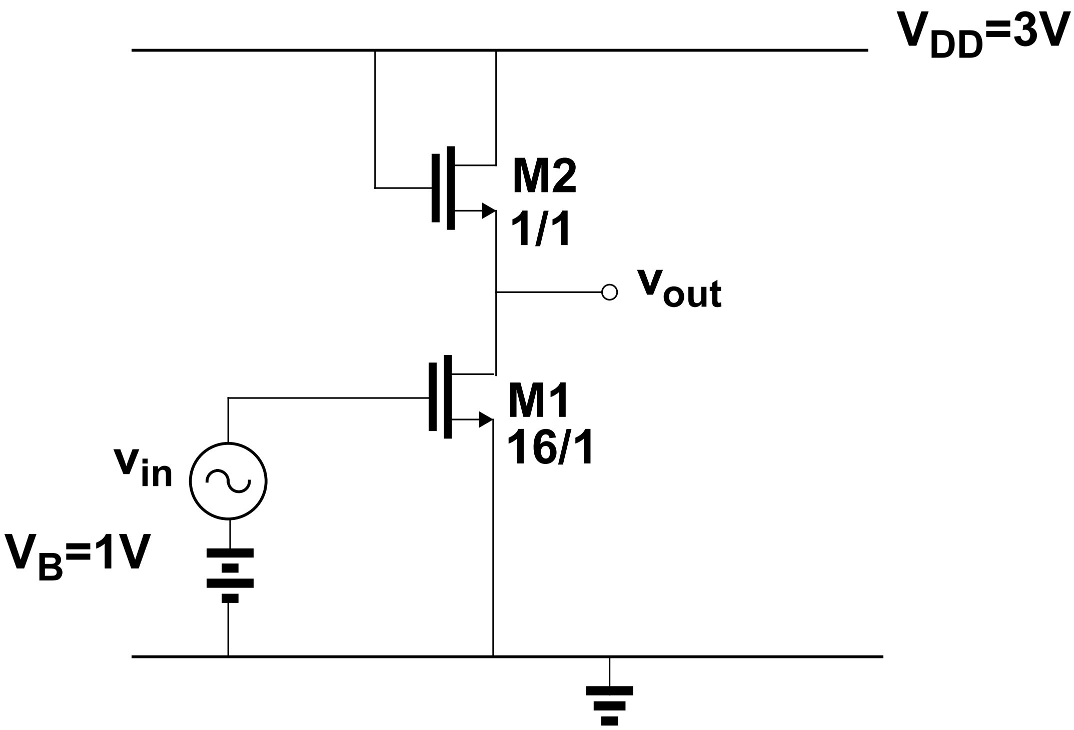

Figure 1

Figure 1 shows a common-source stage with an NMOS diode load.
Biasing and transistor dimensions are as shown in Figure 1. Take $K_n^{'}=200\mu A/V^2$, $V_{tn} = 0.75V$.

(i) Draw the small-signal equivalent circuit for the circuit shown in Figure 1.

(ii) Derive an expression for the small-signal voltage gain (v_{out}/v_{in}) in terms of the small-signal transistor parameters of M1 and M2.

(iii) Show that M1 is in saturation.
What is the headroom of M1 (i.e. the amount by which V_{DS} of M1 exceeds the minimum value of V_{DS} required by M1 to be in saturation)?
Calculate the small-signal voltage gain in dB.
Assume $g_{m1}, g_{m2} >> g_{ds1}, g_{ds2}$.

(iv) The gain of the circuit is increased by changing only the W/L ratio of M1.
What is the maximum value of W/L such that M1 is still in saturation?
What is the small-signal voltage gain in dB with this value of W/L?

Question 2

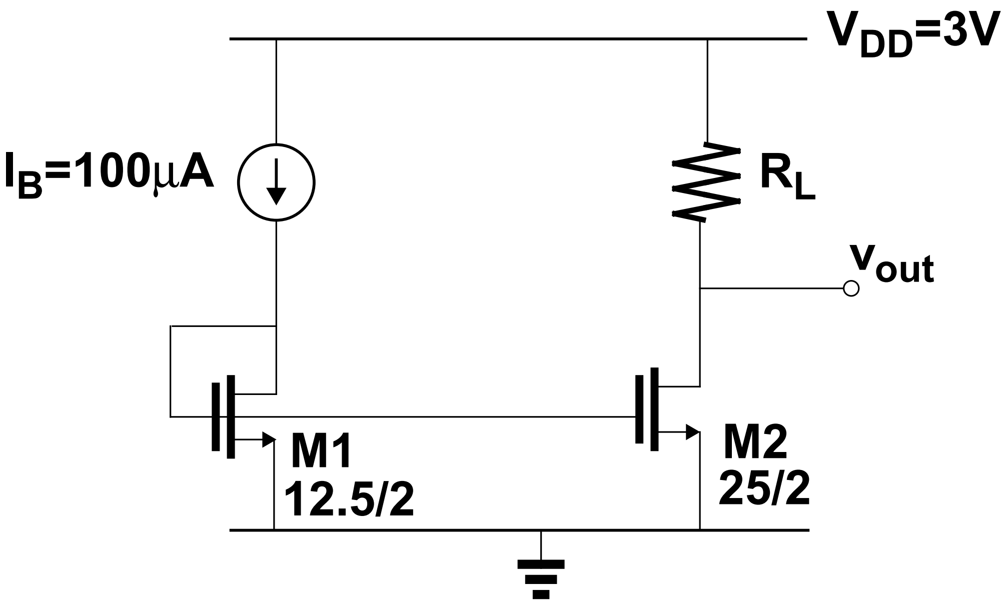

Figure 2

Figure 2 shows an NMOS current mirror (M1, M2) with the output connected via a resistor R_L to V_{DD}.
Biasing and transistor dimensions are as shown in Figure 2.
Take $K_n'=200\mu A/V^2$, $V_{tn}= 0.75V$.

(i) What is the minimum value of the voltage at the output node (i.e the drain of M2) such that M2 is in saturation? What is the maximum value of R_L such that M2 is in saturation?
(ii) Draw a small-signal equivalent circuit showing how to measure the small-signal output resistance of the circuit i.e. the resistance looking into the node v_{out}.
(iii) Derive an expression for the small-signal output resistance in terms of R_L and the small-signal transistor parameters.
(iv) Calculate the small-signal output resistance if R_L is equal to the maximum value calculated in (i). Take λ_n=0.04/L V^{-1} with L in microns.

Question 3

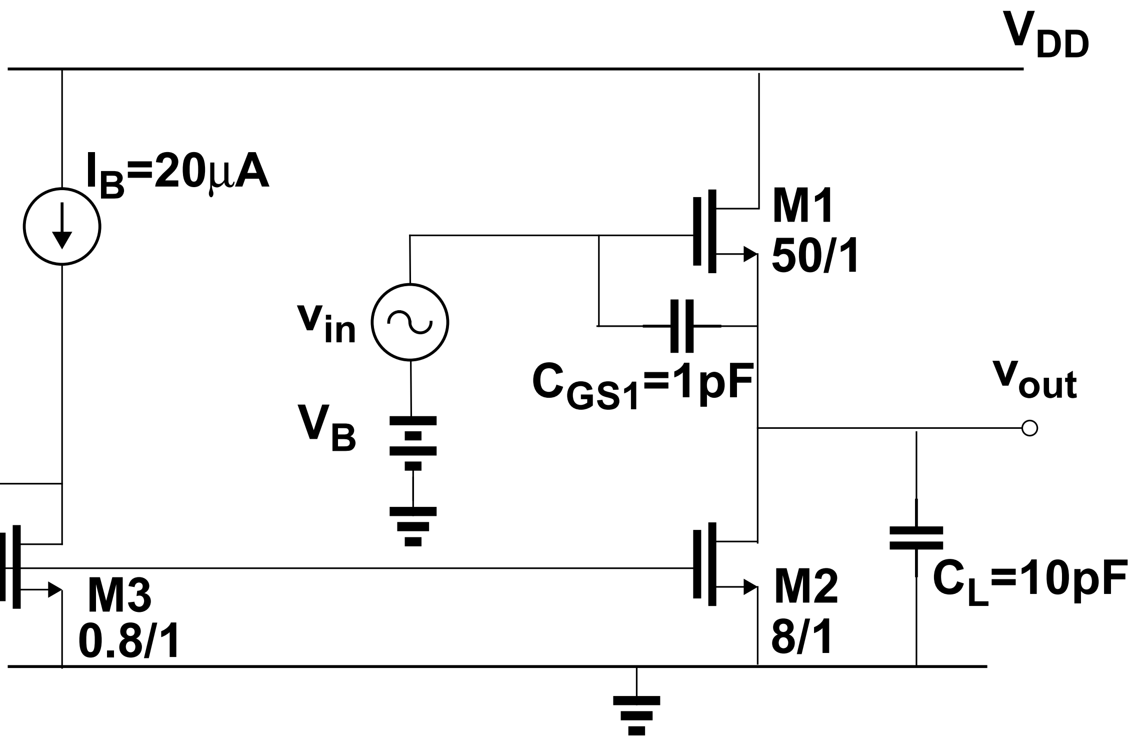

Figure 3

Figure 3 shows an NMOS source follower.

Biasing and transistor dimensions are as shown in Figure 3. Take K_n'=200μA/V^2.

Assume all transistors are in saturation and $g_{m1}, g_{m2} >> g_{ds1}, g_{ds2}$.

(i) Draw the small-signal equivalent circuit for the source follower stage shown in Figure 3.

(ii) Derive an expression for the high-frequency transfer function.

(iii) Calculate the dc gain in dB, and the break frequencies (i.e. pole and/or zero frequencies).

(iv) Draw a Bode diagram of the gain response.
What is the value of gain at frequencies well above the break frequencies?

Question 4

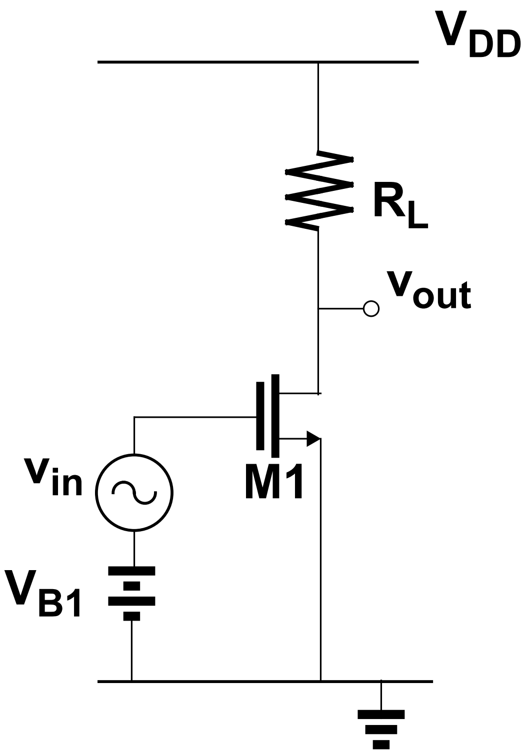

Figure 4a

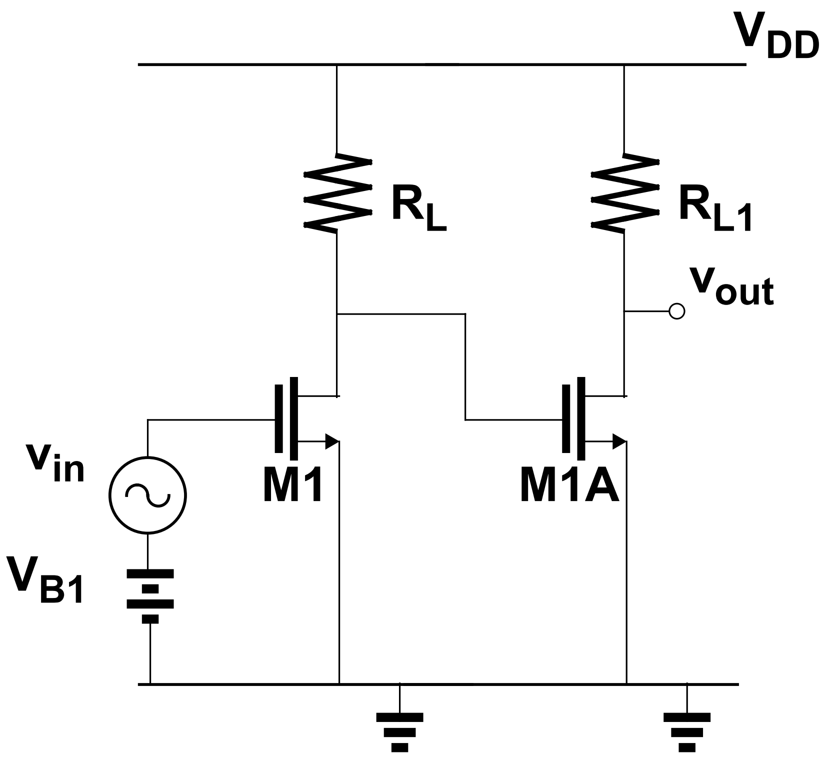

Figure 4b

For the circuits shown in Figure 4a and 4b, assume all transistors are operating in saturation.
Only thermal noise sources need be considered.
Take Boltzmann's constant $k=13.8 \times 10^{-24}$ J/°K, temperature T=300°K.

(i) Draw the small-signal model for the circuit shown in Figure 4a.
What is the low-frequency small-signal voltage gain (v_{out}/v_{in}) in terms of R_L and the small-signal parameters of M1?

(ii) What is the input-referred noise voltage density in terms of the small-signal parameters of M1, R_L, Boltzmann's constant k and temperature T?

(iii) Calculate the input-referred noise voltage density if g_{m1}=400µA/V, R_L=10kΩ.
What is the noise voltage density at the output? Assume $g_{ds1} << 1/R_L$.
(Note: the units µA/V are equivalent to µS).

(iv) The gain stage shown in Figure 4a is cascaded with an identical gain stage, with identical transistor dimensions and load resistance as shown in Figure 4b. Assume also that M1A has the same biasing conditions as M1.
Calculate the input-referred noise voltage density of the circuit shown in Figure 4b.
What is the total input-referred noise in a bandwidth of 1MHz to 10MHz?